

VLSI Interconnect – HW03 – due 16 Ordibehesht

Consider a transmission line with length x excited with an arbitrary input v_s through a source impedance Z_s and terminated with a load impedance Z_l , as shown in Fig.1. A general transmission line can be considered as a distributed zy (in contrast with distributed rlc) where $z(s)$ is the impedance per unit length and $y(s)$ is the admittance per unit length of the line as shown in Fig. 2.

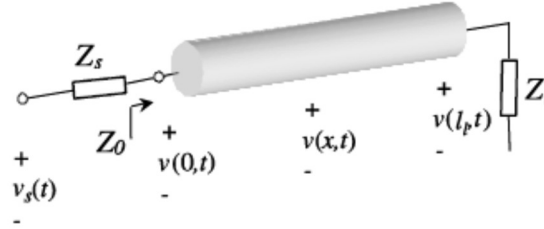


Figure 1

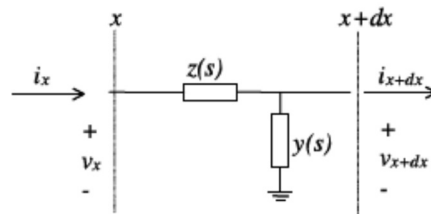


Figure 2

1. Show that the transfer function of a T-line can be written as:

$$H(s) = \frac{v_o(s)}{v_{in}(s)} = k_1(1 + k_3) \frac{e^{-\gamma x}}{1 - k_2 k_3 e^{-2\gamma x}}$$

where

$$k_1 = \frac{Z_0}{Z_s + Z_0} ; k_2 = \frac{Z_s - Z_0}{Z_s + Z_0} ; k_3 = \frac{Z_l - Z_0}{Z_l + Z_0} ; \gamma = \sqrt{zy} ; Z_0 = \sqrt{z/y}$$

2. As we discussed in the course, normalizing a line ($z(s) = r + sl, y(s) = sc$) to a line with unity time-of-flight (T_F) and characteristic impedance makes all equations shorter and comparisons easier. Suppose an rlc line with length x is driven by a source with an impedance of $R_s + sL_s$ and is terminated by a load capacitance C_l . The concepts that are used for the normalization are as follows:

- i. An rlc line with length x , can be replaced by $(xr)(xl)(xc)$ line with unity length
- ii. Multiplication of all impedances of any linear circuit by a certain value does not change the voltage-voltage transfer function of the system; therefore, all impedances can be multiplied by the reciprocal of characteristic impedance of the line, Z_0 ,
- iii. Finally, time-frequency duality implies that shrinking time by T_F is the same as multiplying all frequencies by the same factor (T_F).

Show that, by using these three concepts, an rlc line with length x can be replaced by an $\tilde{r}11$ line with unity length. The following relations between timing in the original and normalized cases, however, should be considered (all normalized parameters are marked with a tilde sign):

$$\tilde{t} = t/T_F ; \tilde{f} = fT_F$$

Other parameters should be also normalized as:

$$\tilde{R}_s = R_s/Z_0 ; \tilde{L}_s = L_s/T_F Z_0 ; \tilde{C}_l = C_l Z_0/T_F ; \tilde{r} = rx/Z_0 ;$$

3. Considering skin effect as $z(s) = r + r'\sqrt{s} + sl$, show that normalized \tilde{r}' can be written as

$$\tilde{r}' = r'x / (Z_0\sqrt{T_F})$$

4. For n-tier design, 2 adjacent levels with orthogonal metal levels are called *pair*, and a *tier* is a collection of pairs with the same pitch (p). For an IC designed in 7.5nm Technology based on [1], fill out Table 1. For \tilde{C}_l consider it can be anything from 5 times C_0 up to 20 times C_0 (as given in Table I of [1], $C_0 = 3.45aF$)

Table 1. Results of n-tier design for 7.5 nm node using Copper wires. Lmax is normalized to the gate pitch (1 GP = 0.1178 μ m)

	Pitch[nm]	L_max[GP]	\tilde{r}'_{min}	\tilde{r}'_{max}	\tilde{r}'_{min}	\tilde{r}'_{max}	\tilde{C}_l_{min}	\tilde{C}_l_{max}
Pair1	15	42						
Pair2	15	842						
Pair3	24.7	4706						
Pair4	49.1	12202						
Pair5	84.7	25240						
Pair6	191.8	70084						
Pair7	220.7	82863						

5. Consider an *rlc* line (with no skin effect) is driving with an ideal source ($Z_s = 0$) and is open ended ($Z_l = \infty$). Rewrite the transfer function with the normalized parameters and plot the root locus of the normalized TF for different values of \tilde{r} . What is the minimum value for \tilde{r} such that the T-line acts like an *rc* line (with real roots)? How can this be considered as the minimum length in the original line?

6. (Extra credit) Redo 5, now considering skin effect ($\tilde{r}' \neq 0$). You may plot the root locus for changes in \tilde{r}' for different values for \tilde{r} . Use data in part 4 for choosing reasonable range for \tilde{r} and \tilde{r}' .

7. Insert optimal buffer insertion for longest line in [1]:

- A. Considering Bakoglu buffer insertion
- B. Considering Cascaded buffer insertion

8. (Extra credit) Use SPICE model (taken from PTM website for 7.5nm [2]) compare your delay calculation with HSPICE results for 7.B. Sweep over the optimal distance between buffers and find x_{opt} based on HSPICE results and compare it with 7.B.

[1] Esmat Kishani Farahani, Reza Sarvari, "Design of n-Tier Multilevel Interconnect Architectures by Using Carbon Nanotube Interconnects." IEEE Trans. VLSI Syst. 23(10), 2015.

[2] <http://ptm.asu.edu/>